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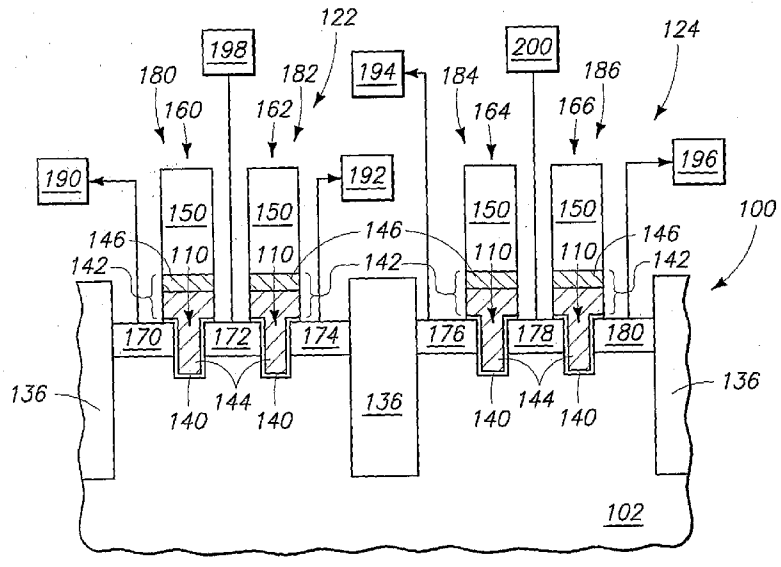
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(54) Title: METHODS OF FORMING RECESSED ACCESS DEVICES



(57) Abstract: The invention includes methods of forming recessed access devices (180, 182, 184, 186). A substrate (102) is provided to have recessed access device trenches therein. A pair of the recessed access device trenches (110) are adjacent one another. Electrically conductive material (144) is formed within the recessed access device trenches, and source/drain regions (170, 172, 174, 176, 178, 180) are formed proximate the electrically conductive material. The electrically conductive material and source/drain regions together are incorporated into a pair of adjacent recessed access devices. After the recessed access device trenches are formed within the substrate, an isolation region trench (130) is formed between the adjacent recessed access devices and filled with electrically insulative material (136) to form a trenched isolation region.

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